

STATUS OF THE CLAIMS

Claims 1-5 (canceled)

Claim 6 (previously amended)

6. (Amended) A method of mounting a semiconductor device on a substrate, comprising the steps of:

forming a composite connection member formed of a core and a conductor covering said core on a first electrode of said semiconductor device;

forming a single-layer connection member formed of a conductor on a second electrode of said semiconductor device;

forming an auxiliary connection part in contact with an upper side of one of the first electrode and the second electrode of said substrate, said auxiliary connection part being formed of a low melting-point conductor having a melting point of at most a melting point of said conductor covering said core; and

matching respective positions of said auxiliary connection part and said composite connection material to bring into contact said auxiliary connection part and said composite connection material, and heating to connect said auxiliary connection part and said composite connection material.

Claims 7-8 (original)

7. The method of mounting a semiconductor device according to claim 6, wherein said auxiliary connection part on the electrode of said substrate is greater in volume than said conductor of said composite connection material on the electrode of said semiconductor device.

8. A mounting structure for mounting a semiconductor device, that is connected to a substrate via a plurality of connection materials, wherein

said plurality of connection materials are constituted of a first type of connection material formed of a core and a conductor covering said core and a second type of connection material formed of a conductor.

Claim 9 (previously and currently amended)

9. (Amended) A mounting structure for mounting a semiconductor device, that is connected to a substrate via a composite connection material formed of a core, ~~and~~ a conductor covering said core, and a single-layer connection material, wherein

said composite connection material and said single-layer connection material ~~have~~ has a substrate contact portion contacting said substrate and an electrode contact portion contacting an electrode of said semiconductor device, respectively, and melting points of said substrate contact portion are both ~~is~~ lower than those ~~that~~ of said electrode contact portions.